

RESPONSE TO FINAL OFFICE ACTION and NOTICE OF APPEAL
Serial No. 10/716,096
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IN THE SPECIFICATION

Please amend the paragraphs beginning on page 1, line 10 as follows:

This application is a continuation of ~~the following United States Patent Applications:~~ ~~United States U.S.~~ Patent Application No. 08/808,246, entitled "CHAMBER FOR CONSTRUCTING A FILM ON A SEMICONDUCTOR WAFER", filed on February 28, 1997[;], now U.S. Patent No. 6,699,530, which is a continuation-in part of U.S. Patent Application No. 08/680,913, entitled "PLASMA BOMBARDING OF THIN FILMS", filed on July 12, 1996[;], now abandoned, which is a continuation-in part of U.S. Patent Application No. 08/677,218, entitled "IN-SITU CONSTRUCTION OF AN OXIDIZED FILM ON A SEMICONDUCTOR WAFER", filed on July 9, 1996[;], now abandoned, which is a continuation-in part of U.S. Patent Application No. 08/677,185, entitled "CHAMBER FOR CONSTRUCTING AN OXIDIZED FILM ON A SEMICONDUCTOR WAFER", filed on July 9, 1996[;], now U.S. Patent No. 6,155,198, which is a continuation-in part of U.S. Patent Application No. 08/567,461, entitled "PLASMA ANNEALING OF THIN FILMS", filed on December 5, 1995[; and]], now abandoned, which is a continuation-in part of U.S. Patent Application No. 08/498,990, entitled "BIASED PLASMA ANNEALING OF THIN FILMS", filed on July 8, 1995, now abandoned.

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